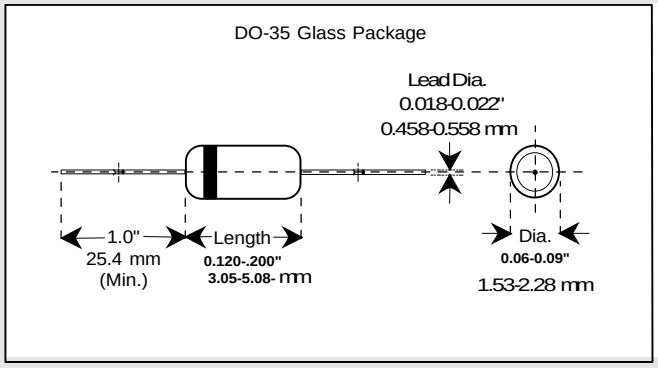
Silicon Switching Diode

1N914
or
1N914-1

DO-35 Glass Package

Applications

Used in general purpose applications, where performance and switching speed are important.



Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- LL-34/35 MELF SMD available
- Full approval to Mil-S-19500/116
- Available up to JANTXV levels
- "S" level screening available to SCDs

Maximum Ratings	Symbol	Value	Unit
Peak Inverse Voltage	PIV	100 (Min.)	Volts
Average Rectified Current	I_{Avg}	75	mAmps
Continuous Forward Current	I_{Fdc}	300	mAmps
Peak Surge Current (t_{peak} = 1 sec.)	I_{peak}	0.5	Amp
Power Dissipation @ T_L=50 °C, L = 3/8" from body	P_{tot}	250	mWatts
Storage & Operating Temperature Range	$T_{St\ \&\ Op}$	-65 to +200	°C

Electrical Characteristics @ 25 °C*	Symbol	Absolute Limits	Unit
Breakdown Voltage @ Ir = 0.1 mA	PIV	100 (Min)	Volts
Reverse Leakage Current @ V_R = 20 V	I_R	0.025 (Max)	µA
Reverse Leakage (Vr =20 V, 150 °C)	I_R	50 (Max)	µA
Reverse Leakage Current @ V_R = 75 V	I_R	5.0 (Max)	µA
Capacitance @ V_R = 0 V, f = 1mHz	C_T	4.0 (Max)	pF
Reverse Recovery Time (note 1)	t_{rr}	4.0 (Max)	nSecs
Forward Recovery Time (note 2)	V_{fr}	2.5 (Max)	Volts

Note 1: I_F = 10 mA, R_L = 100 Ohms, Vr = 6.0 Volts , Irr =1.0 mA

Note 2: I_F = 50 mA dc

***UNLESS OTHERWISE SPECIFIED**

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